



# HiPerFET™ Power MOSFET

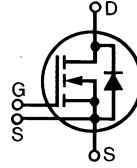
Single MOSFET Die

Preliminary data sheet

**IXFE 36N100**  
**IXFE 34N100**

$V_{DSS}$	$I_{D25}$	$R_{DS(on)}$
<b>1000 V</b>	<b>33 A</b>	<b>0.24 <math>\Omega</math></b>
<b>1000 V</b>	<b>30 A</b>	<b>0.28 <math>\Omega</math></b>

**$t_{rr} \leq 250$  ns**



## Symbol Test Conditions

## Maximum Ratings

$V_{DSS}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	1000	V
$V_{DGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ , $R_{GS} = 1\text{M}\Omega$	1000	V
$V_{GS}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$	36N100	33 A
		34N100	30 A
$I_{DM}$	$T_C = 25^\circ\text{C}$ ; Note 1	36N100	144 A
		34N100	136 A
$I_{AR}$	$T_C = 25^\circ\text{C}$	36	A
$E_{AR}$	$T_C = 25^\circ\text{C}$	64	mJ
$E_{AS}$	$T_C = 25^\circ\text{C}$	4	J
$dv/dt$	$I_S \leq I_{DM}$ , $di/dt \leq 100$ A/ $\mu\text{s}$ , $V_{DD} \leq V_{DSS}$ $T_J \leq 150^\circ\text{C}$ , $R_G = 2 \Omega$	5	V/ns
$P_D$	$T_C = 25^\circ\text{C}$	580	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$T_L$	1.6 mm (0.063 in) from case for 10 s	300	$^\circ\text{C}$
$V_{ISOL}$	50/60 Hz, RMS $t = 1$ min $I_{ISOL} \leq 1$ mA $t = 1$ s	2500	V~
		3000	V~
$M_d$	Mounting torque	1.5/13 Nm/lb.in.	
	Terminal connection torque	1.5/13 Nm/lb.in.	
<b>Weight</b>		19	g

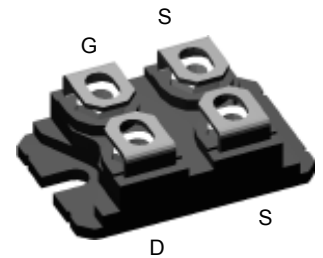
## Symbol Test Conditions

( $T_J = 25^\circ\text{C}$ , unless otherwise specified)

## Characteristic Values

		Min.	Typ.	Max.
$V_{DSS}$	$V_{GS} = 0$ V, $I_D = 3$ mA	1000		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 8$ mA	3.0		5.0 V
$I_{GSS}$	$V_{GS} = \pm 20$ V, $V_{DS} = 0$ V			$\pm 200$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ $V_{GS} = 0$ V	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$		100 $\mu\text{A}$ 2 mA
$R_{DS(on)}$	$V_{GS} = 10$ V, $I_D = I_T$ Note 2	36N100 34N100		0.24 $\Omega$ 0.28 $\Omega$

## ISOPLUS 227™ (IXFE)



G = Gate  
S = Source  
D = Drain

Either Source terminal at miniBLOC can be used as Main or Kelvin Source

## Features

- Conforms to SOT-227B outline
- Low  $R_{DS(on)}$  HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
- Fast intrinsic Rectifier

## Applications

- DC-DC converters
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- Temperature and lighting controls

## Advantages

- Low cost
- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 10\text{ V}; I_D = I_T$ , Note 2	18	28	S
$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		15000	pF
$C_{oss}$			1400	pF
$C_{rss}$			340	pF
$t_{d(on)}$ $t_r$ $t_{d(off)}$ $t_f$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = I_T$ $R_G = 1\ \Omega$ (External),		81	ns
			82	ns
			150	ns
			40	ns
$Q_{g(on)}$ $Q_{gs}$ $Q_{gd}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = I_T$		455	nC
			120	nC
			185	nC
$R_{thJC}$ $R_{thCK}$			0.22	K/W
			0.07	K/W

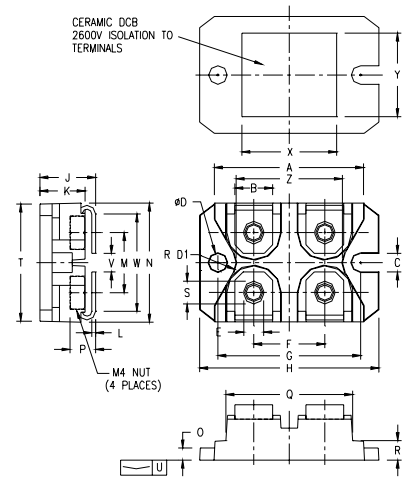
### Source-Drain Diode

( $T_J = 25^\circ\text{C}$ , unless otherwise specified)

Symbol	Test Conditions	Characteristic Values			
		Min.	Typ.	Max.	
$I_S$	$V_{GS} = 0$	36N100 34N100		36 34	A A
$I_{SM}$	Repetitive; pulse width limited by $T_{JM}$	36N100 34N100		144 136	A A
$V_{SD}$	$I_F = I_S, V_{GS} = 0\text{ V}$ , Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$			1.3	V
$t_{rr}$	$I_F = I_S, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$	$T_J = 25^\circ\text{C}$ $T_J = 25^\circ\text{C}$ $T_J = 25^\circ\text{C}$	180 30 2		ns ns $\mu\text{C}$
$Q_{RM}$ $I_{RM}$			8		A

- Notes:
1. Pulse width limited by  $T_{JM}$ .
  2. Pulse test,  $t \leq 300\text{ ms}$ , duty cycle  $d \leq 2\%$ .
  3.  $I_T$  Test current:  
IXFE36N100:  $I_T = 18\text{ A}$   
IXFE34N100:  $I_T = 17\text{ A}$

### ISOPLUS-227 B



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.240	1.270	31.50	32.26
B	.310	.330	7.87	8.38
C	.155	.165	3.94	4.19
D	.155	.165	3.94	4.19
D1	.150	.157	3.81	3.98
E	.160	.168	4.06	4.27
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.489	1.505	37.80	38.23
J	.465	.481	11.81	12.22
K	.370	.380	9.40	9.65
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.100	.105	2.54	2.67
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.160	.170	4.06	4.32
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.001	.002	-0.03	0.05
V	.130	.160	3.30	4.06
W	.780	.830	19.81	21.08
X	.770	.810	19.56	20.57
Y	.680	.720	17.27	18.29
Z	.885	.892	22.48	22.66

Please see IXFN36N100 data sheet for characteristic curves.